

# MOSFET

## OptiMOS™ 3 Power-Transistor, 100 V

### Features

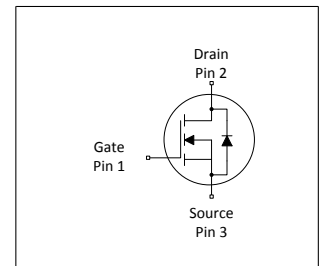
- Ideal for high frequency switching and sync. rec.
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

### Product validation

Qualified according to JEDEC Standard

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	100	V
$R_{DS(on),max}$	12.6	m $\Omega$
$I_D$	35	A
$Q_{oss}$	35	nC
$Q_G(0V..10V)$	26	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
IPA126N10NM3S	PG-TO220 FullPAK	126N103S	-

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	$I_D$	-	-	35 25	A	$V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	-	-	140	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	-	-	90	mJ	$I_D=35\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	33	W	$T_C=25\text{ °C}$
Operating and storage temperature	$T_j$ , $T_{stg}$	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	4.5	°C/W	-

## 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.0	2.7	3.5	V	$V_{DS}=V_{GS}$ , $I_D=45\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	1	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	10.9 13.5	12.6 -	m $\Omega$	$V_{GS}=10\text{ V}$ , $I_D=35\text{ A}$ $V_{GS}=6\text{ V}$ , $I_D=18\text{ A}$
Gate resistance	$R_G$	-	1.1	-	$\Omega$	-
Transconductance	$g_{fs}$	-	50	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$ , $I_D=35\text{ A}$

<sup>1)</sup> See Diagram 3 for more detailed information

<sup>2)</sup> See Diagram 13 for more detailed information

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance <sup>1)</sup>	$C_{iss}$	-	1880	2500	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$	-	330	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance	$C_{rss}$	-	14	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	12	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=35\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Rise time	$t_r$	-	6	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=35\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Turn-off delay time	$t_{d(off)}$	-	20	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=35\text{ A}$ , $R_{G,ext}=1.6\ \Omega$
Fall time	$t_f$	-	4	-	ns	$V_{DD}=50\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=35\text{ A}$ , $R_{G,ext}=1.6\ \Omega$

**Table 6 Gate charge characteristics<sup>2)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	9	-	nC	$V_{DD}=50\text{ V}$ , $I_D=35\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	5	-	nC	$V_{DD}=50\text{ V}$ , $I_D=35\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	5	-	nC	$V_{DD}=50\text{ V}$ , $I_D=35\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	9	-	nC	$V_{DD}=50\text{ V}$ , $I_D=35\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total <sup>1)</sup>	$Q_g$	-	26	35	nC	$V_{DD}=50\text{ V}$ , $I_D=35\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.7	-	V	$V_{DD}=50\text{ V}$ , $I_D=35\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	24	-	nC	$V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge	$Q_{oss}$	-	35	-	nC	$V_{DD}=50\text{ V}$ , $V_{GS}=0\text{ V}$

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	30	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	140	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.9	1.2	V	$V_{GS}=0\text{ V}$ , $I_F=35\text{ A}$ , $T_j=25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	58	-	ns	$V_R=50\text{ V}$ , $I_F=35\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$	-	114	-	nC	$V_R=50\text{ V}$ , $I_F=35\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

### 4 Electrical characteristics diagrams

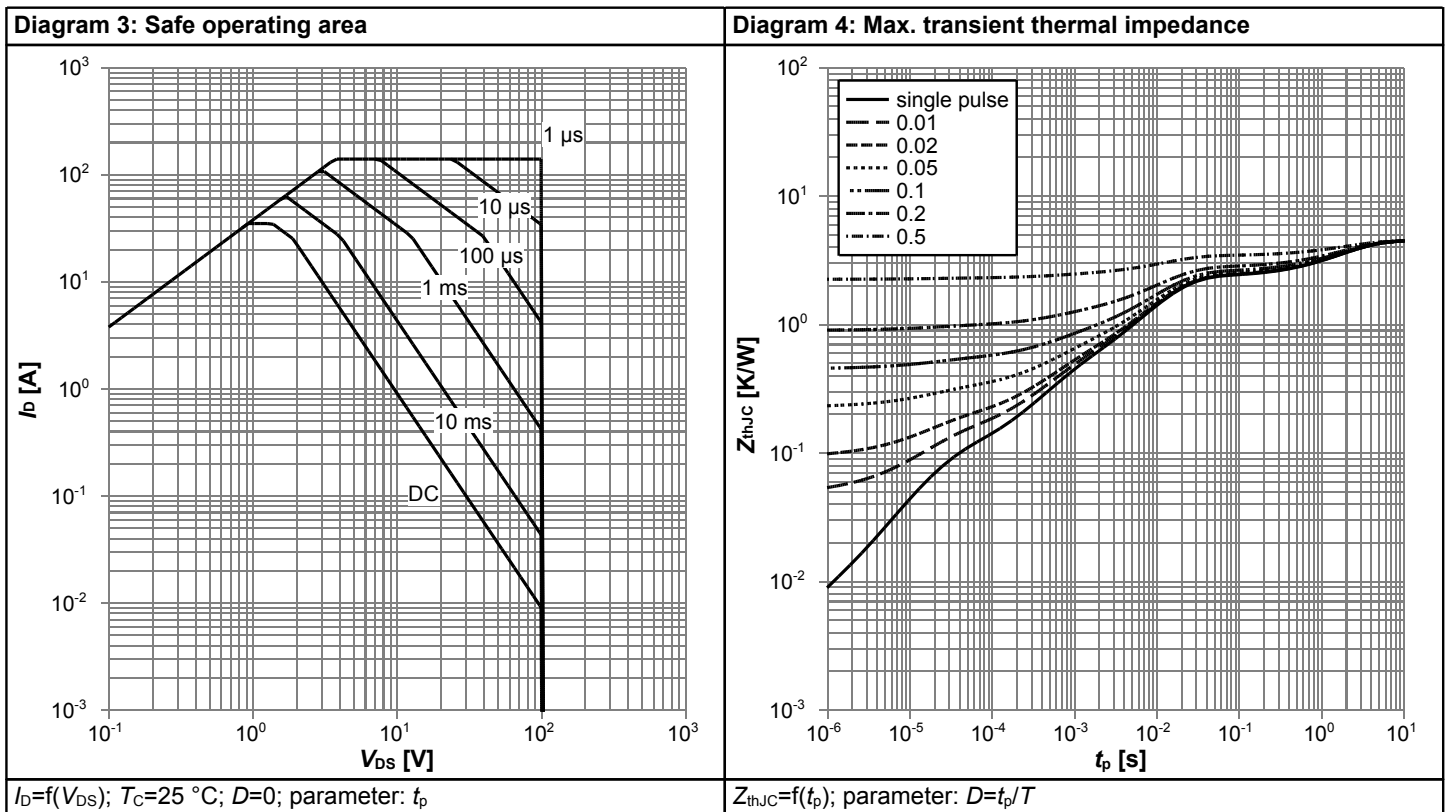
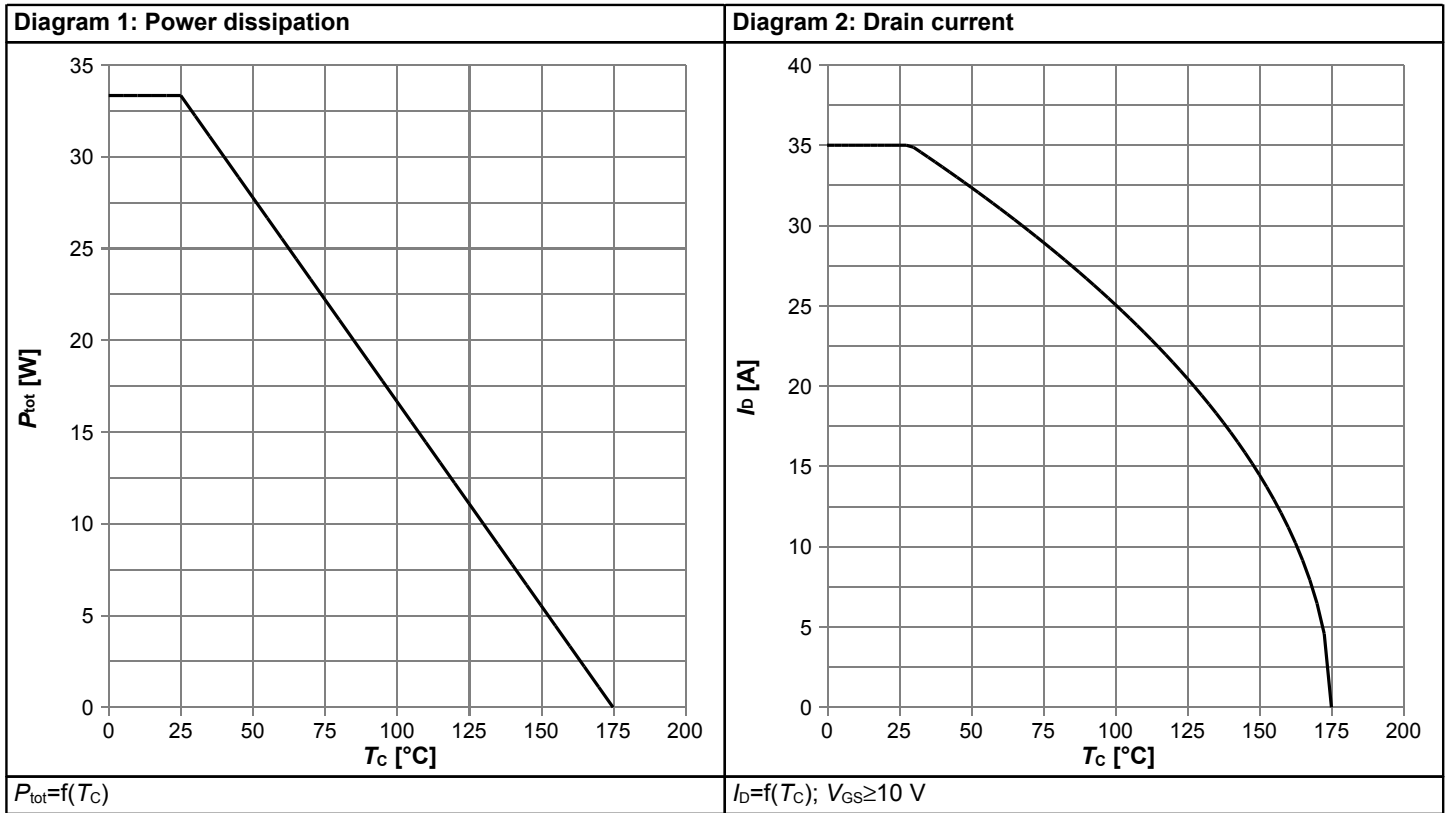
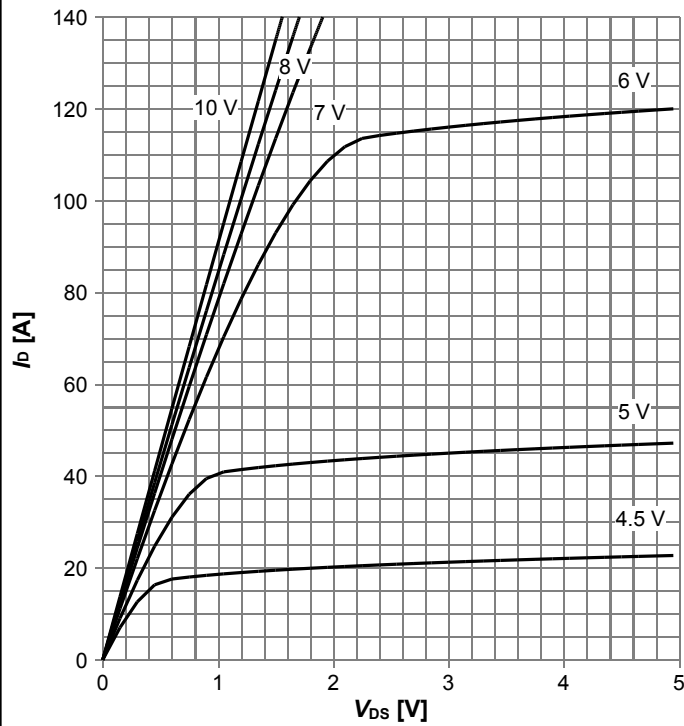
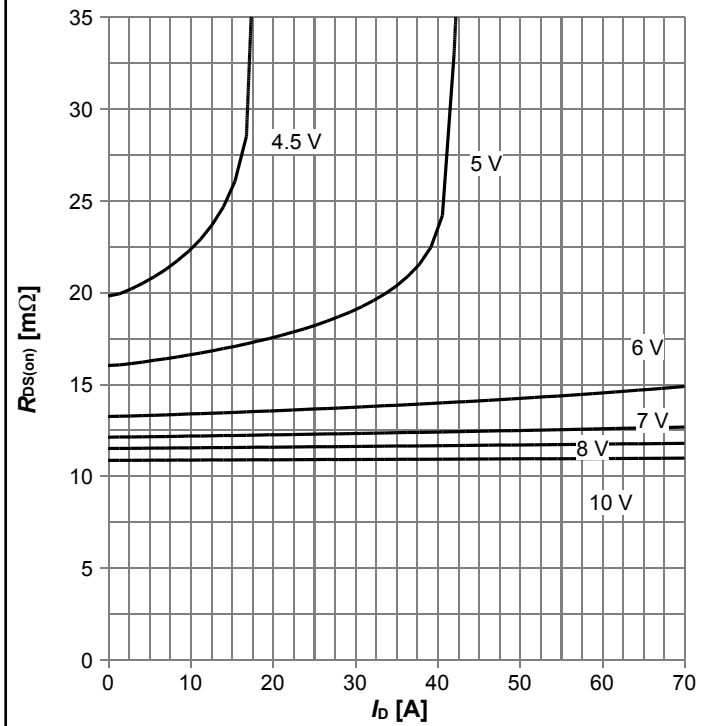


Diagram 5: Typ. output characteristics



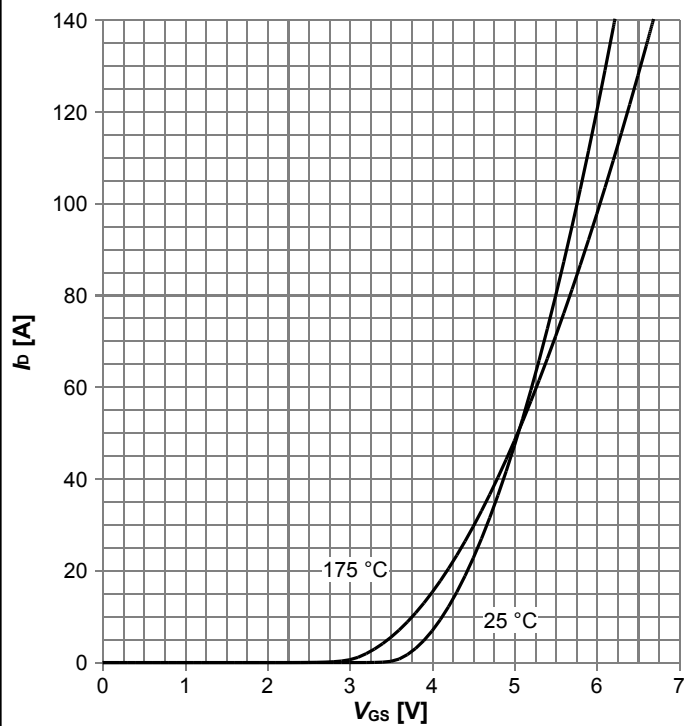
$I_D = f(V_{DS})$ ,  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



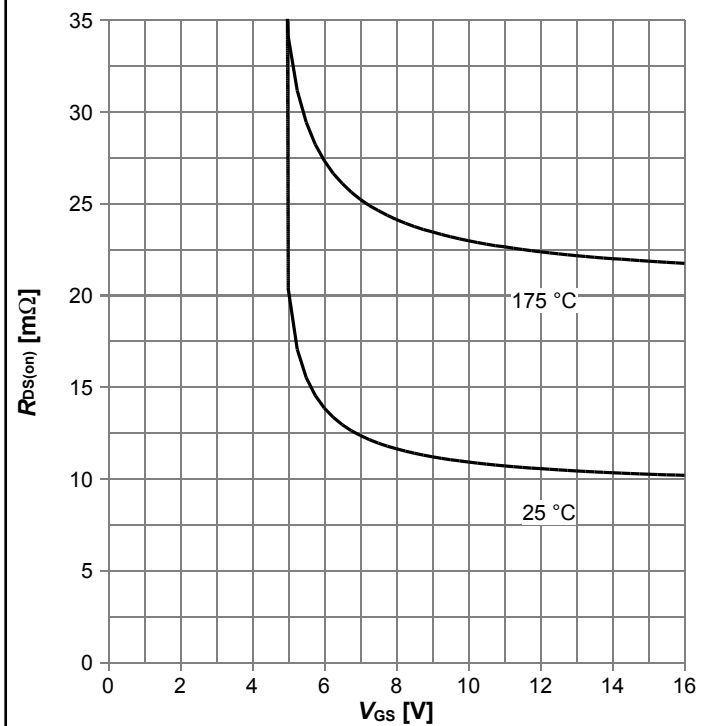
$R_{DS(on)} = f(I_D)$ ,  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



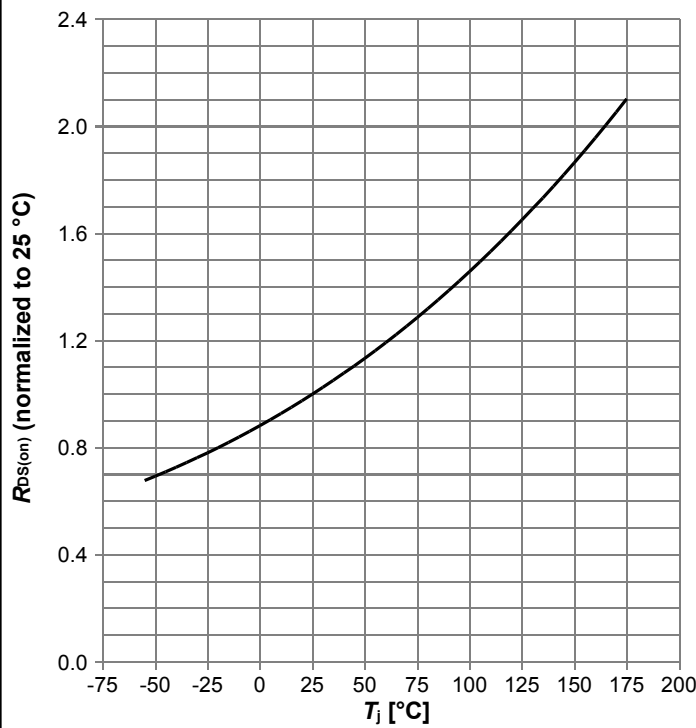
$I_D = f(V_{GS})$ ,  $|V_{DS}| > 2|I_D|R_{DS(on)max}$ ; parameter:  $T_j$

Diagram 8: Typ. drain-source on resistance



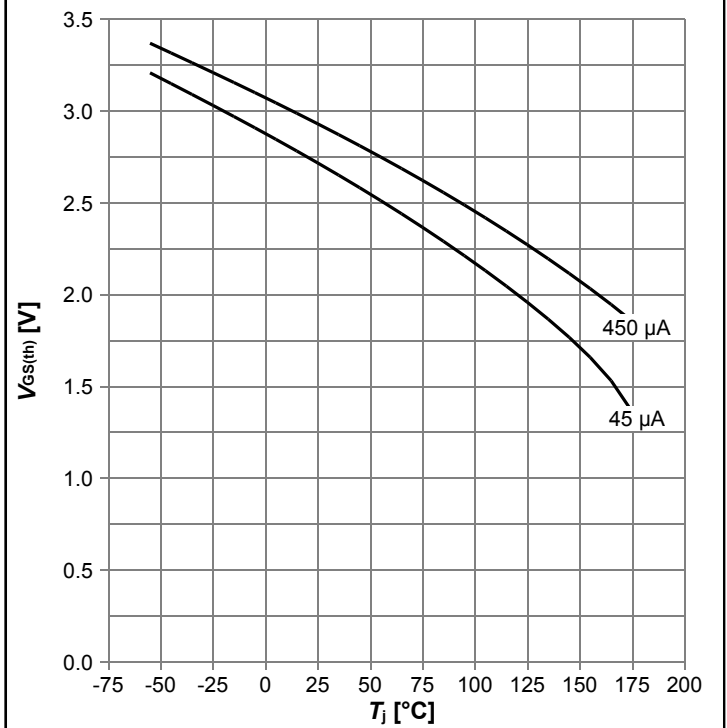
$R_{DS(on)} = f(V_{GS})$ ,  $I_D = 35\text{ A}$ ; parameter:  $T_j$

Diagram 9: Normalized drain-source on resistance



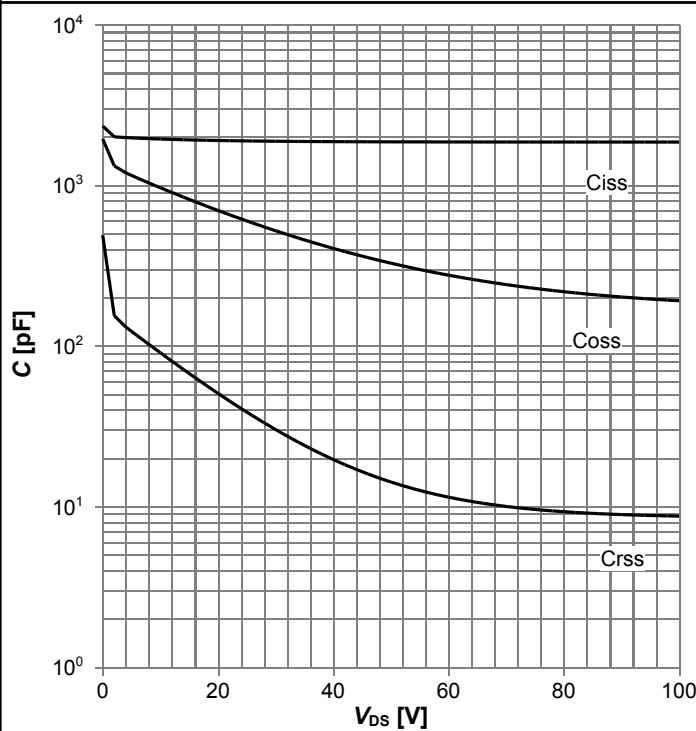
$R_{DS(on)}=f(T_j)$ ,  $I_D=35$  A,  $V_{GS}=10$  V

Diagram 10: Typ. gate threshold voltage



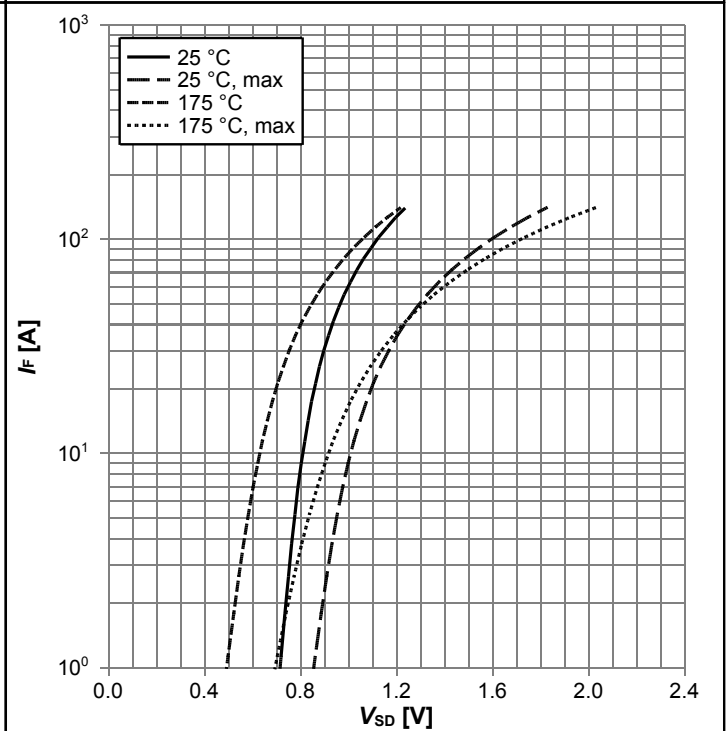
$V_{GS(th)}=f(T_j)$ ,  $V_{GS}=V_{DS}$ ; parameter:  $I_D$

Diagram 11: Typ. capacitances



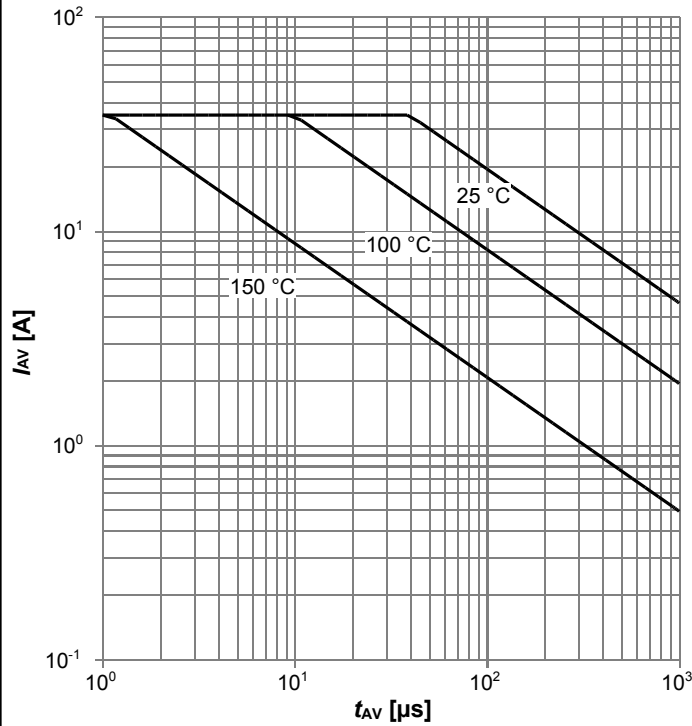
$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

Diagram 12: Forward characteristics of reverse diode



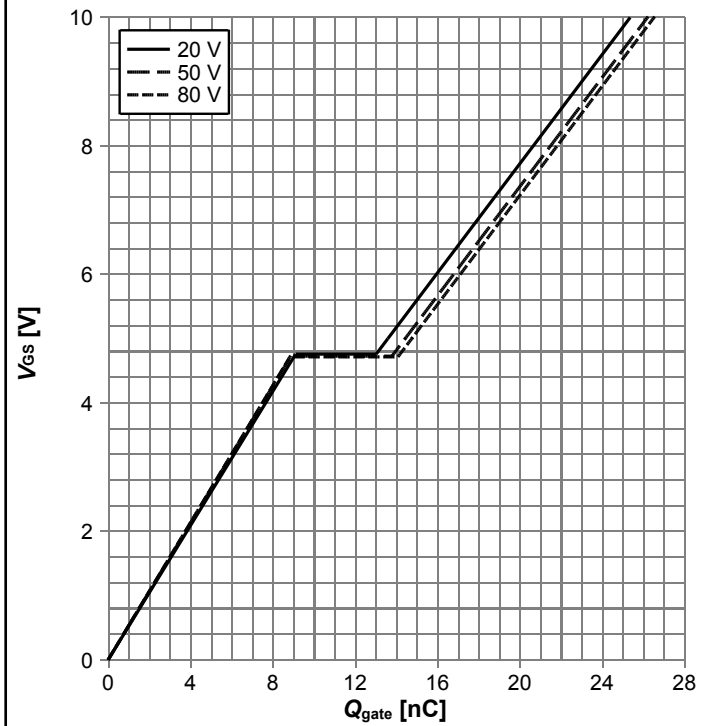
$I_F=f(V_{SD})$ ; parameter:  $T_j$

**Diagram 13: Avalanche characteristics**



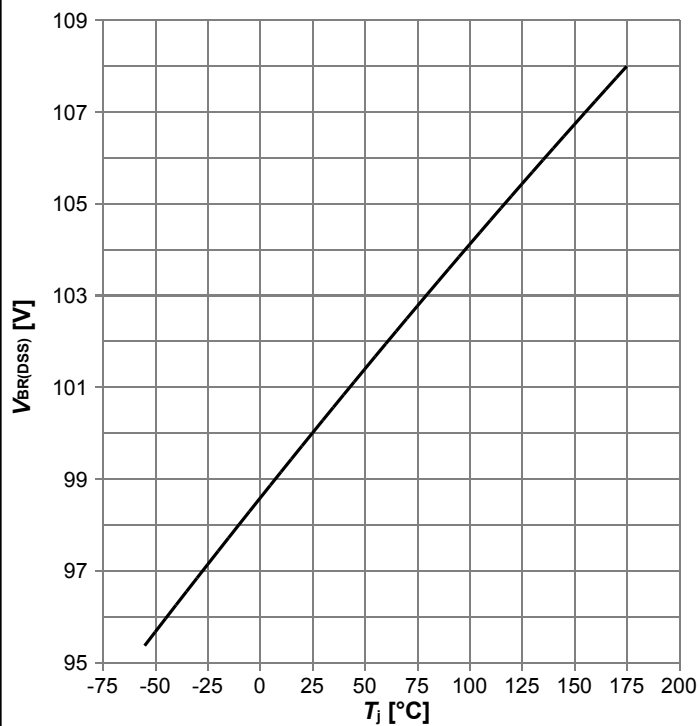
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j,start}$

**Diagram 14: Typ. gate charge**



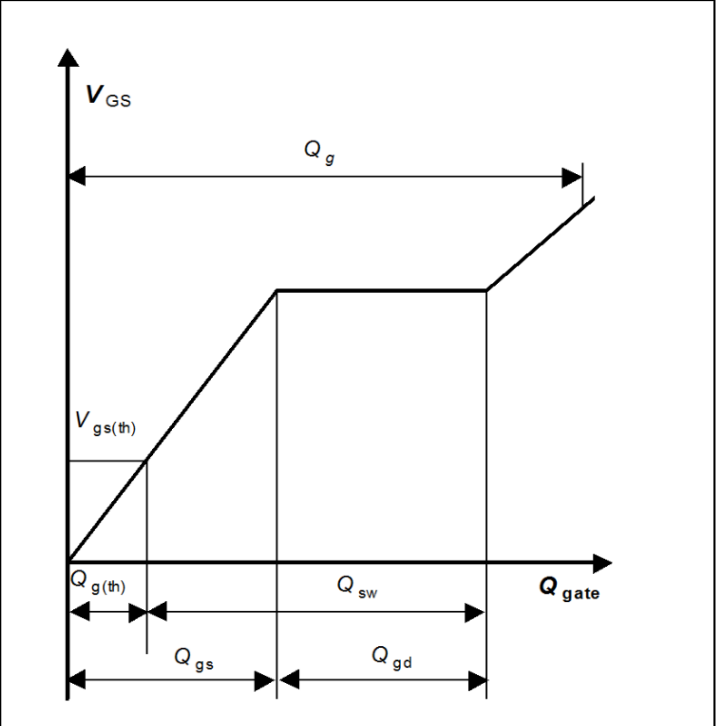
$V_{GS}=f(Q_{gate}), I_D=35 \text{ A pulsed}, T_j=25 \text{ °C}$ ; parameter:  $V_{DD}$

**Diagram 15: Drain-source breakdown voltage**

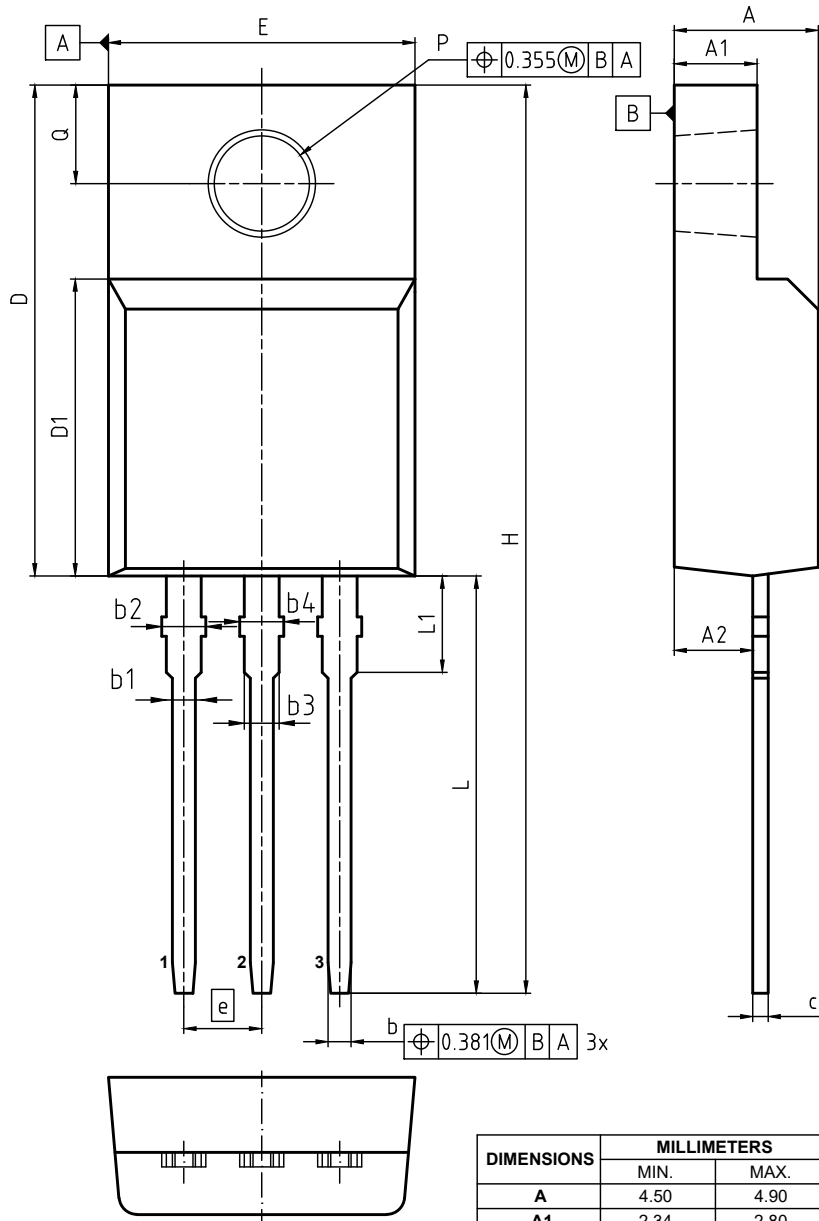


$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

**Diagram Gate charge waveforms**



## 5 Package Outlines



NOTES:  
STANDARD QUALITY GRADE  
DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS

DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.50	4.90
A1	2.34	2.80
A2	2.42	2.86
b	0.65	0.90
b1	0.95	1.38
b2	1.20	1.50
b3	0.65	1.38
b4	1.20	1.50
c	0.40	0.63
D	15.67	16.15
D1	8.97	9.83
E	10.00	10.65
e	2.54	
H	28.70	29.75
L	12.78	13.75
L1	2.83	3.45
øP	3.00	3.38
Q	3.15	3.50

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Figure 1 Outline PG-TO220 FullPAK, dimensions in mm/inches

## Revision History

IPA126N10NM3S

**Revision: 2023-06-06, Rev. 2.2**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-07-22	Release of final version
2.1	2019-09-02	Update package outline
2.2	2023-06-06	Update current rating and footnotes

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